

P-Channel 40 V (D-S) MOSFEET

PRODUCT SUMMARY					
V _{DS} (V)	R _{DS(on)} (mΩ)	I _D (A)			
- 40	5 at V _{GS} = - 10 V	- 85 ^d			
	7.3 at V _{GS} = - 4.5 V	- 70 ^d			

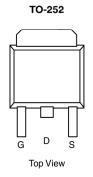
FEATURES

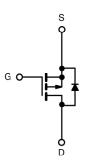
- DT-Trench Power MOSFET
- 100 % Rg and UIS Tested



APPLICATIONS

- Load Switch
- DC/DC Converter





P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)						
Parameter	Symbol	Limit	Unit			
Drain-Source Voltage		V _{DS}	- 40			
Gate-Source Voltage			± 20	V		
Continuous Drain Current (T, = 175 °C)	T _C = 25 °C	- I _D	- 85 ^d	A		
Softania da Brain Garrent (1) = 170 G/	T _C = 125 °C		- 50			
Pulsed Drain Current	I _{DM}	- 320	A			
Avalanche Current single pulse	I _{AS}	- 80				
Avalanche Energy single pulse ^a	L = 0.1 mH	E _{AS}	55	mJ		
Power Dissipation	T _C = 25 °C	P _D	105 ^c	W		
Fower Dissipation	T _A = 25 °C	'D	3.9 ^{b, c}			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
l Ai A - A Li Ab	t ≤ 10 s	- R _{thJA}	20	30	°C/W	
Junction-to-Ambient ^D	Steady State		40	60		
Junction-to-Case		R _{thJC}	-	2.0		

Notes:

- a. Duty cycle \leq 1 %.
- b. When mounted on 1" square PCB (FR-4 material).
- c. See SOA curve for voltage derating.
- d. Package limited.

1 Rev. B



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static	0.						
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 40				
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = - 40 V, V _{GS} = 0 V			- 1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 32 V, V _{GS} = 0 V, T _J = 125 °C			- 50 μA		
		V _{DS} = - 32 V, V _{GS} = 0 V, T _J = 150 °C			- 100		
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 85			Α	
	D	V _{GS} = - 10 V, I _D = - 30 A		5	6	mΩ	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = -20 \text{ A}$		7.3	9		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 5 V, I _D = - 30 A	30 A			S	
Dynamic ^b							
Input Capacitance	C _{iss}			6250		pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = -20 \text{ V}, f = 1 \text{ MHz}$		530			
Reverse Transfer Capacitance	C _{rss}			470			
Total Gate Charge ^c	Qg			86			
Gate-Source Charge ^c	Q _{gs}	V _{DS} = - 20 V, V _{GS} = - 10 V, I _D = -30 A		30		nC	
Gate-Drain Charge ^c	Q _{gd}			17		1	
Turn-On Delay Time ^c	t _{d(on)}			35			
Rise Time ^c	t _r	$V_{DD} = -20 \text{ V}, R_{L} = 0.6 \Omega$		20			
Turn-Off Delay Time ^c	t _{d(off)}	$I_{D} = -30 \text{ A}, V_{GEN} = -10 \text{ V}, R_{G} = 6\Omega$		82		ns	
Fall Time ^c	t _f			55			
Source-Drain Diode Ratings and Cha	aracteristics	Γ _C = 25 °C ^b					
Continuous Current	Is				-85	Α	
Forward Voltage ^a	V _{SD}	I _F = - 1 A, V _{GS} = 0 V		- 0.7	- 1.0	٧	
Reverse Recovery Time	t _{rr}	I _F = - 30 A, dI/dt = 100 A/μs		48		ns	
Reverse Recovery Charge	Q_{rr} $I_F = -30 \text{ A, dI/dt} = 100 \text{ A/}\mu\text{s}$			62		nC	

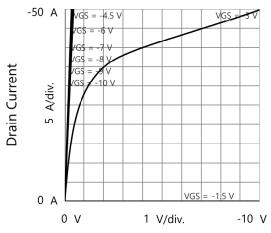
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

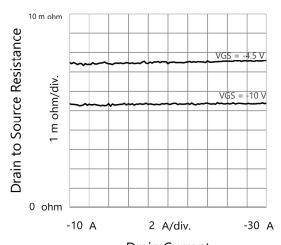




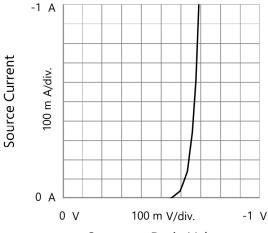
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



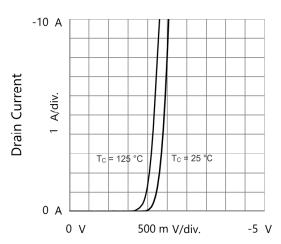
Drain to Source Voltage Output Characteristics



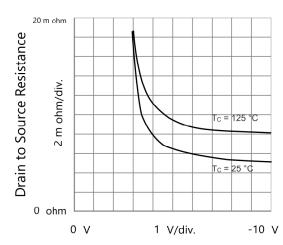
Drain Current
Drain to Source Resistance vs. Drain Current



Source to Drain Voltage Body Diode Forward Characteristics

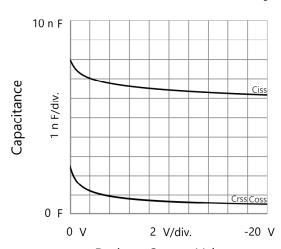


Gate to Source Voltage Transfer Characteristics



Gate to Source Voltage

Drain to Source Resistance vs. Gate to Source Voltage

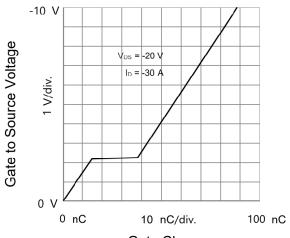


Drain to Source Voltage Capacitances

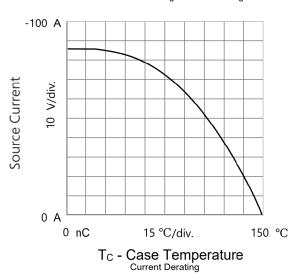


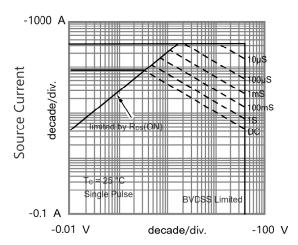


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

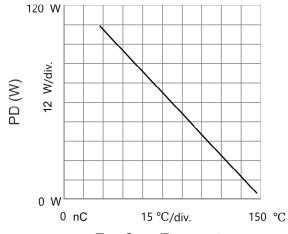








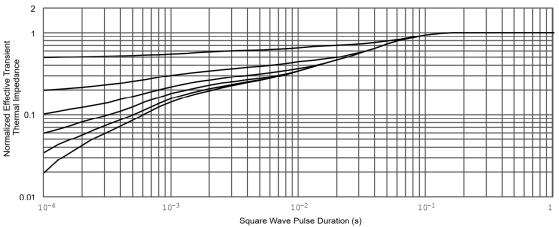
Source to Drain Voltage Safe Operating Area, Junction-to-Ambient



 T_{C} - Case Temperature $_{\text{Power Derating}}$

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

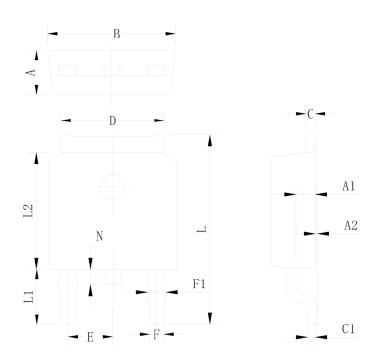
Note

- The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)
- are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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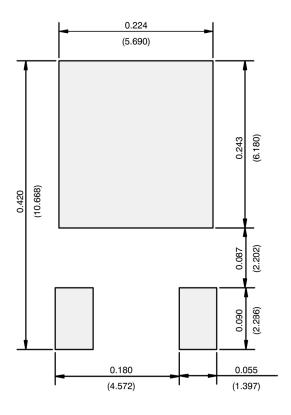
TO-252-2L PACKAGE OUTLINE DIMENSIONS



UNIT:mm

Symbol	Min	Тур	Max	
A	2.20	2.30	2.40	
A1	0.91	1.01	1.11	
A2	0.05	0.15	0.25	
В	6.45	6.60	6.75	
С	0.45	0.50	0.58	
C1	0.45	0.50	0.58	
D	5.12	5.32	5.52	
Е	2.286 TYP			
F	0.66	0.76	0.86	
F1	0.66	0.86	1.06	
L	9.60	9.90	10.20	
L1	2.6	2.8	3.0	
L2	5.95	6.10	6.25	
N	0.60	0.80	1.00	

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)





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